



NTE2409 Silicon PNP Transistor General Purpose Amp, Surface Mount (Compl to NTE2408)

Description:

The NTE2409 is a silicon PNP general purpose transistor in a SOT-23 type surface mount package designed for use in driver stages of audio amplifiers in thick and thin-film hybrid circuits.

Absolute Maximum Ratings:

Collector-Base Voltage, V_{CBO}	80V
Collector-Emitter Voltage, V_{CEX}	80V
Collector-Emitter Voltage, V_{CEO}	65V
Emitter-Base Voltage, V_{EBO}	5V
Collector Current, I_C	
Continuous	100mA
Peak	200mA
Peak Emitter Current, I_{EM}	200mA
Peak Base Current, I_{BM}	200mA
Total Power Dissipation ($T_A = +60^\circ\text{C}$, Note 1), P_{tot}	200mW
Junction Temperature, T_J	$+150^\circ\text{C}$
Storage Temperature Range, T_{stg}	-65° to $+150^\circ\text{C}$
Thermal Resistance, Junction-to-Tab, R_{thJT}	60K/W
Thermal Resistance, Tab-to-Soldering Points, R_{thTS}	280K/W
Thermal Resistance, Soldering Points-to-Ambient (Note 1), R_{thSA}	90K/W

Note 1. Mounted on a ceramic substrate .314 (8mm) x .393 (10mm) x .027 (0.7mm).

Electrical Characteristics: ($T_J = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 30\text{V}$, $I_E = 0$	—	1	15	nA
		$V_{CB} = 30\text{V}$, $I_E = 0$, $T_J = +150^\circ\text{C}$	—	—	4	μA
Base-Emitter Voltage	V_{BE}	$V_{CE} = 5\text{V}$, $I_C = 2\text{mA}$, Note 2	600	650	750	mV
		$V_{CE} = 5\text{V}$, $I_C = 10\text{mA}$, Note 2	—	—	820	mV
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}$, $I_B = 0.5\text{mA}$, Note 3	—	75	300	mV
		$I_C = 100\text{mA}$, $I_B = 5\text{mA}$, Note 3	—	250	650	mV

Note 2. V_{BE} decreases by about 2mV/K with increasing temperature.

Note 3. $V_{BE(sat)}$ decreases by about 1.7mV with increasing temperature.

Electrical Characteristics (Cont'd): ($T_J = +25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$, Note 3	–	700	–	mV
		$I_C = 100\text{mA}, I_B = 5\text{mA}$, Note 3	–	850	–	mV
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$	220	–	475	
Transition Frequency	f_T	$V_{CE} = 5\text{V}, I_C = 10\text{mA}, f = 35\text{MHz}$	–	150	–	MHz
Collector Capacitance	C_c	$V_{CB} = 10\text{V}, I_E = I_e = 0, f = 1\text{MHz}$	–	4.5	–	pF
Small–Signal Current Gain	h_{fe}	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$	75	–	900	
Noise Figure	NF	$V_{CE} = 5\text{V}, I_C = 200\mu\text{A}, f = 1\text{kHz}, B = 200\text{Hz}, R_S = 2\text{k}\Omega$	–	2	10	dB

Note 3. $V_{BE(sat)}$ decreases by about 1.7mV with increasing temperature.

